



Description

The HSTD10P6F6 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -60V$ $I_D = -10A$

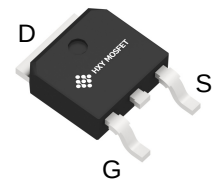
$R_{DS(ON)} < 140m\Omega$ @ $V_{GS}=10V$

Application

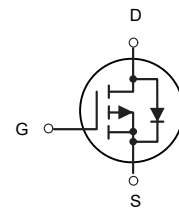
Brushless motor

Load switch

Uninterruptible power supply



TO-252-2L
(DPAK)



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HSTD10P6F6	TO-252-2L(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-10	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-8.3	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-3.3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-2.7	A
I_{DM}	Pulsed Drain Current ²	-26	A
EAS	Single Pulse Avalanche Energy ³	29.8	mJ
I_{AS}	Avalanche Current	-24.4	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	31.3	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4.0	$^\circ C/W$



P-Channel Electrical Characteristics (T_J =25 °C, unless otherwise noted)

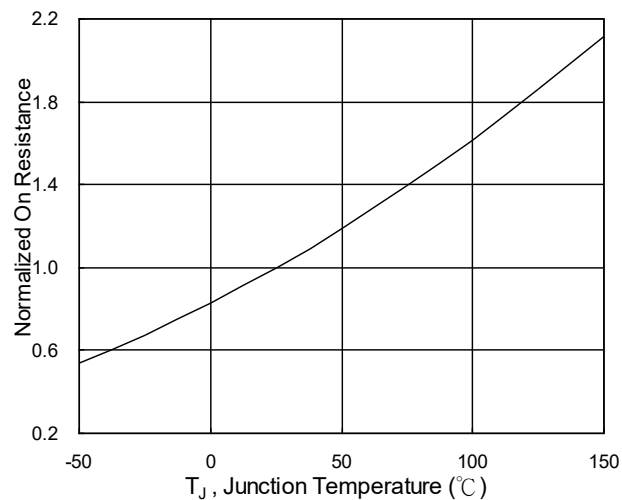
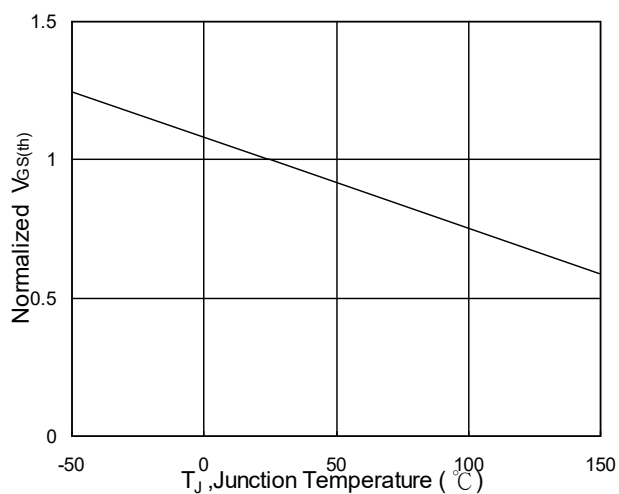
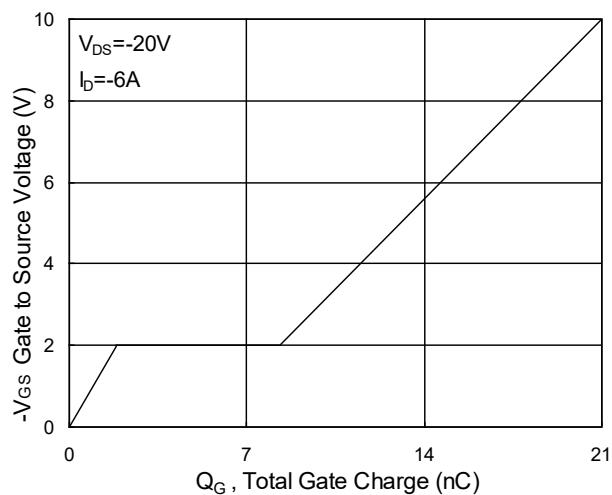
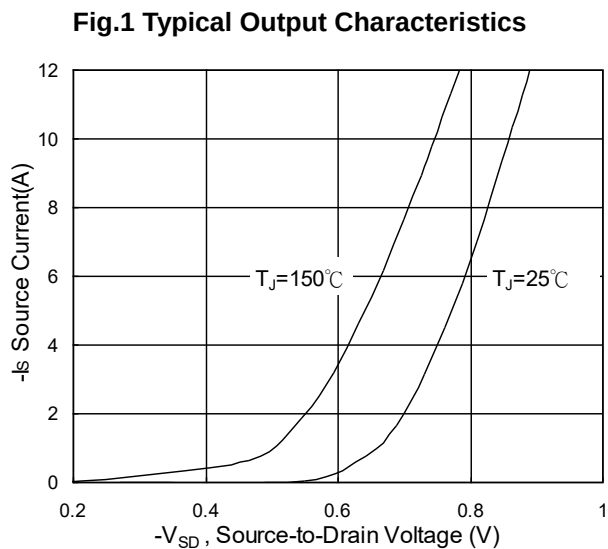
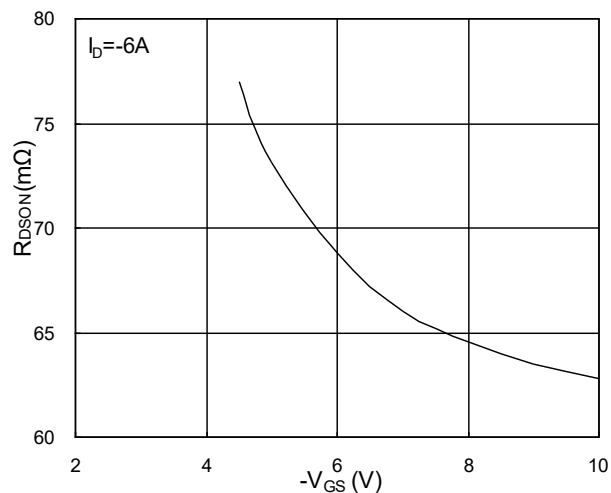
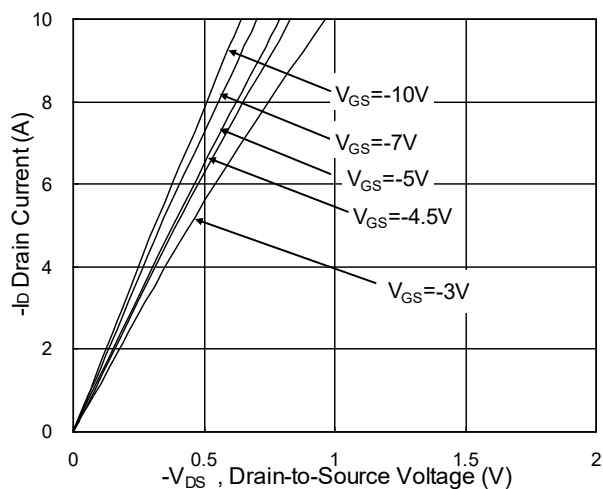
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60	---	---	V
ΔBVDSS/ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =-1mA	---	-0.03	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-3A	---	125	140	mΩ
		V _{GS} =-4.5V , I _D =-2A	---	185	200	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	1.6	-2.5	V
IDSS	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-48V , V _{GS} =0V , T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-3A	---	8.5	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-48V , V _{GS} =-4.5V , I _D =-3A	---	12.1	---	nC
Q _{gs}	Gate-Source Charge		---	2.2	---	
Q _{gd}	Gate-Drain Charge		---	6.3	---	
Td(on)	Turn-On Delay Time	V _{DD} =-15V , V _{GS} =-10V , R _G =3.3Ω , I _D =-1A	---	9.2	---	ns
T _r	Rise Time		---	20.1	---	
Td(off)	Turn-Off Delay Time		---	46.7	---	
T _f	Fall Time		---	9.4	---	
Ciss	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz	---	1137	---	pF
Coss	Output Capacitance		---	76	---	
Crss	Reverse Transfer Capacitance		---	50	---	
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-13	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C	---	---	-1.2	V

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 20Z copper.
- 2、 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、 The EAS data shows Max. rating . The test condition is V DD =-25V,V GS =-10V,L=0.1mH,IAS =-24A
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.



P-Channel Typical Characteristics



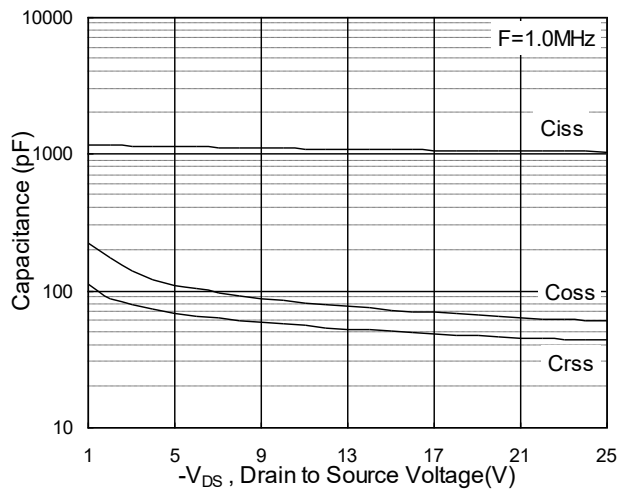


Fig.7 Capacitance

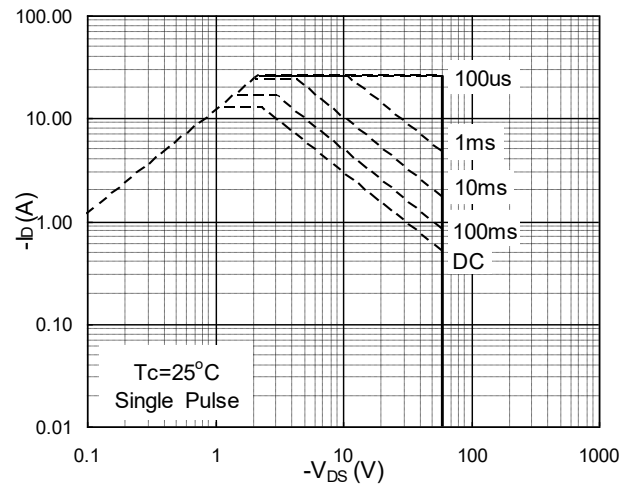


Fig.8 Safe Operating Area

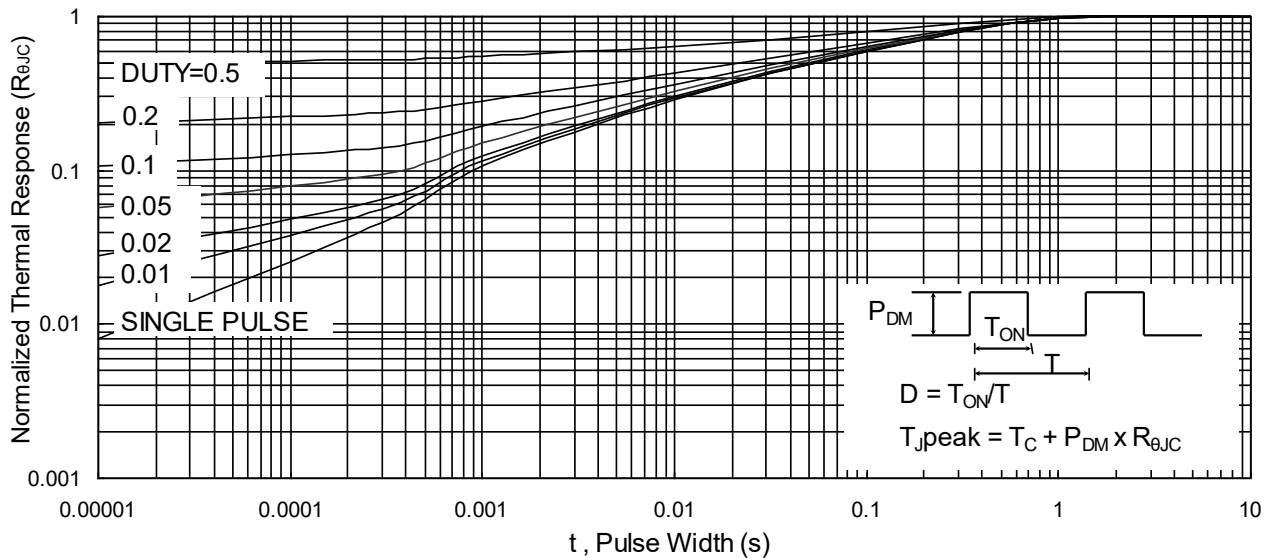


Fig.9 Normalized Maximum Transient Thermal Impedance

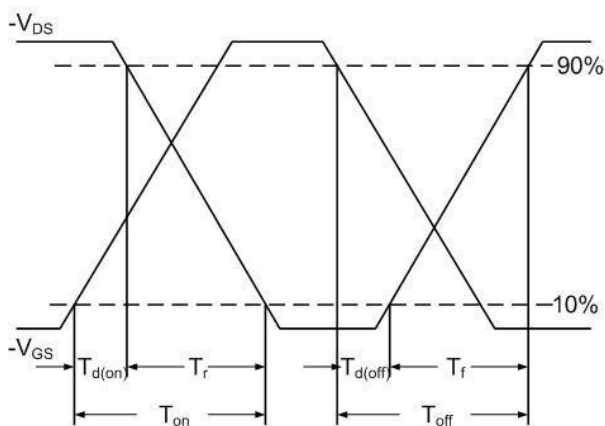


Fig.10 Switching Time Waveform

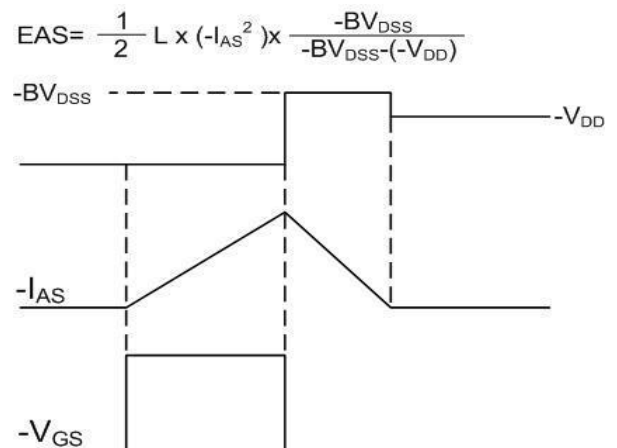
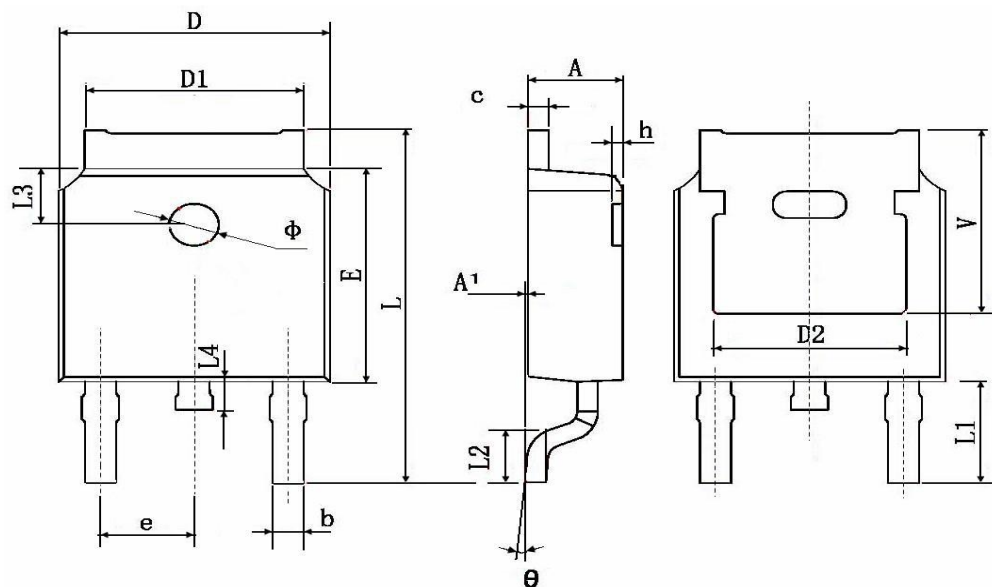


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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